



## JCD30SL065A SiC Schottky Diode

Rev.2.2

### DESCRIPTION

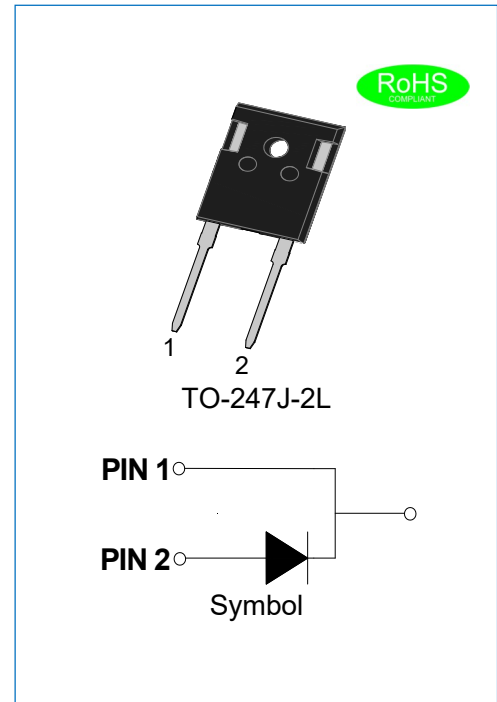
- ✧ 650V Schottky diode
- ✧ Zero reverse recovery current
- ✧ Zero forward recovery voltage
- ✧ High frequency operation
- ✧ Switching characteristics independent of temperature
- ✧ Fast switch
- ✧ Positive temperature coefficient of forward voltage ( $V_F$ )

### BENEFIT

- ✧ Lower switching loss
- ✧ No thermal runaway in parallel devices
- ✧ Lower heatsink dependent

### APPLICATION

- ✧ Switch mode power supplies(SMPS)
- ✧ Boost diodes in PFC or DC/DC stages
- ✧ Free wheeling diodes in inverter stages
- ✧ AC/DC converters



### ABSOLUTE MAXIMUM RATING (Rating at 25°C junction temperature unless otherwise specified.)

Parameter	Symbol	Value	Unit
Maximum repetitive peak reverse voltage	$V_{RRM}$	650	V
Maximum DC blocking voltage	$V_{DC}$	650	V
Average forward current	$T_C=150^{\circ}C$ $I_{F(AV)}$	30*	A
Repetitive peak forward surge current	$t_P=10ms, T_C=25^{\circ}C$ $I_{FRM}$	200*	A
Non-repetitive peak forward surge current	$t_P=10ms, T_C=25^{\circ}C$ $I_{FSM}$	240*	A
Non-repetitive peak forward surge current	$T_C=25^{\circ}C, t_P=10\mu s,$ Pulse $I_{FMax}$	1600*	A
Power dissipation	$T_C=25^{\circ}C$ $T_C=110^{\circ}C$ $P_{tot}$	283* 123*	W
Operating junction temperature range	$T_j$	-55 to +175	$^{\circ}C$
Storage temperature range	$T_{stg}$	-55 to +175	$^{\circ}C$

**ELECTRICAL CHARACTERISTICS**(Rating at 25°C junction temperature unless otherwise specified.)

Parameter	Conditions	Symbol	Value			Unit
			Min.	Typ.	Max.	
Forward voltage	$I_F=30A, T_j=25^{\circ}C$	$V_F$	-	1.45	1.80	V
	$I_F=30A, T_j=175^{\circ}C$		-	1.95	2.40	
Reverse current	$V_R=650V, T_j=25^{\circ}C$	$I_R$	-	2	20	$\mu A$
	$V_R=650V, T_j=175^{\circ}C$		-	40	200	
Total capacitance	$V_R=0V, f=1MHz$	C	-	2050	-	pF
	$V_R=200V, f=1MHz$		-	162	-	
	$V_R=400V, f=1MHz$		-	137	-	
Total capacitance charge	$V_R=400V, T_j=25^{\circ}C$	$Q_C$	-	85	-	nC
Capacitance stored energy	$V_R=400V$	$E_C$	-	21	-	$\mu J$

**THERMAL CHARACTERISTICS**

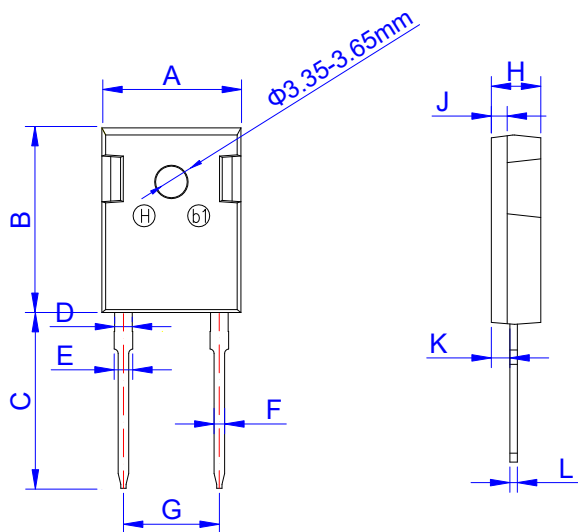
Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction to case	0.53	$^{\circ}C/W$

Note: \*per leg, \*\*per device

**ORDERING INFORMATION**

<p><b>J</b></p> <p>JieJie Microelectronics Co., Ltd</p> <p>SiC Schottky Diode</p>	<p><b>CD</b></p> <p><math>I_F(AV)=30A</math></p>	<p><b>30</b></p>	<p><b>SL</b></p> <p>SL: TO-247J-2L</p>	<p><b>065</b></p> <p><math>V_{RRM}:650V</math></p>	<p><b>A</b></p> <p>Version A</p>
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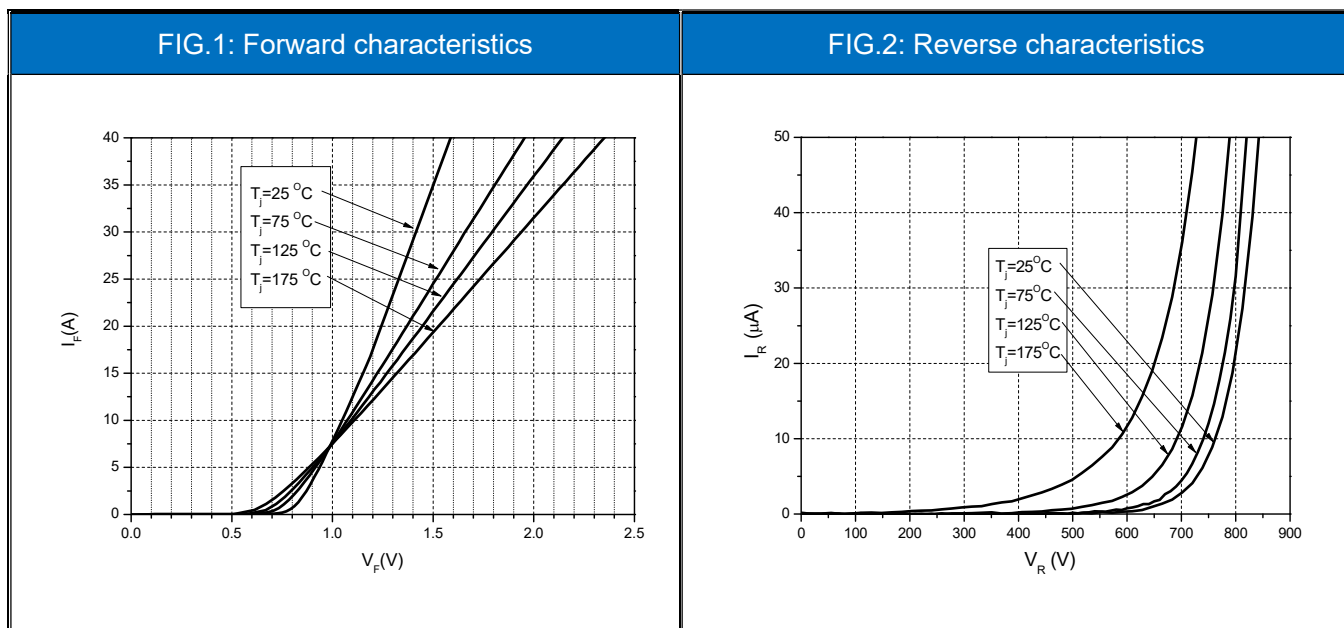
PACKAGE MECHANICAL DATA



TO-247J-2L

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	15.50	15.80	16.10	0.610	0.622	0.634
B	20.80	21.00	21.20	0.819	0.827	0.835
C	19.70	20.00	20.30	0.776	0.787	0.799
D	1.80	2.00	2.20	0.071	0.079	0.087
E	1.90	2.10	2.30	0.075	0.083	0.091
F	1.00	1.20	1.40	0.039	0.047	0.055
G	10.50		11.30	0.413		0.445
H	4.80	5.00	5.20	0.189	0.197	0.205
J	1.90	2.00	2.10	0.075	0.079	0.083
K	2.20	2.35	2.50	0.087	0.093	0.098
L	0.41	0.60	0.79	0.016	0.024	0.031

CHARACTERISTICS CURVE



CHARACTERISTICS CURVE

FIG.3: Capacitance vs. reverse voltage

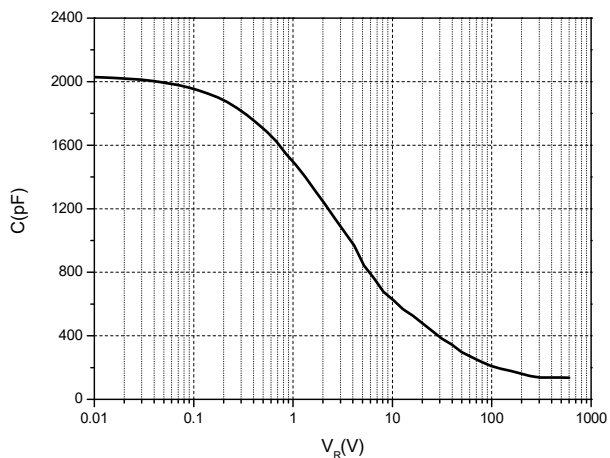


FIG.4: Transient thermal impedance

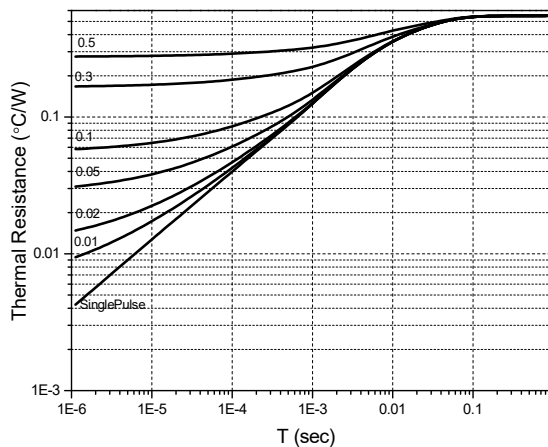


FIG.5: Capacitance charge vs. reverse voltage

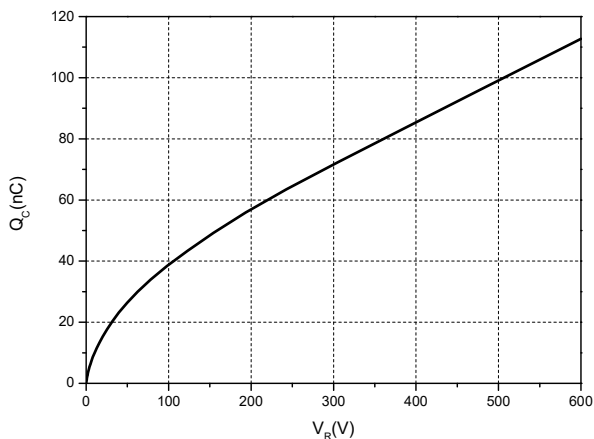


FIG.6: Capacitance stored energy

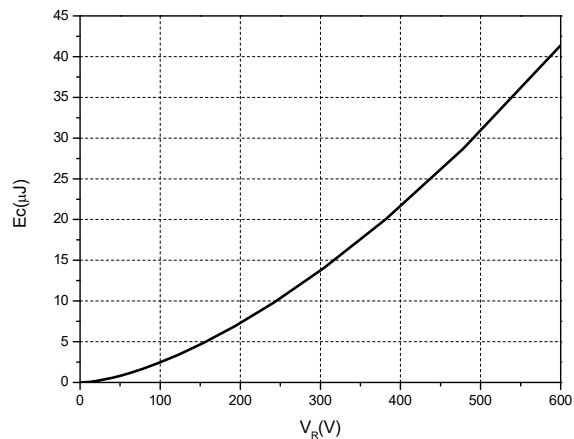


FIG.7: Power derating

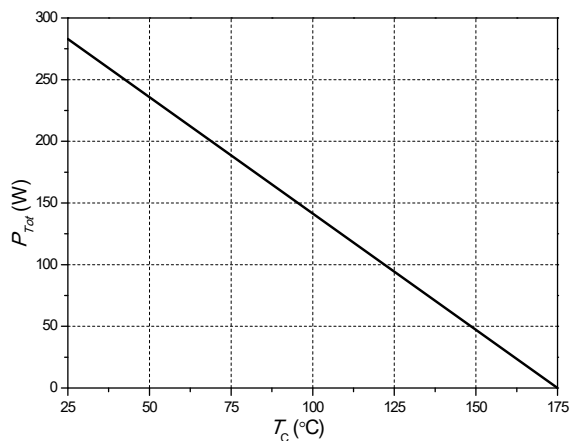
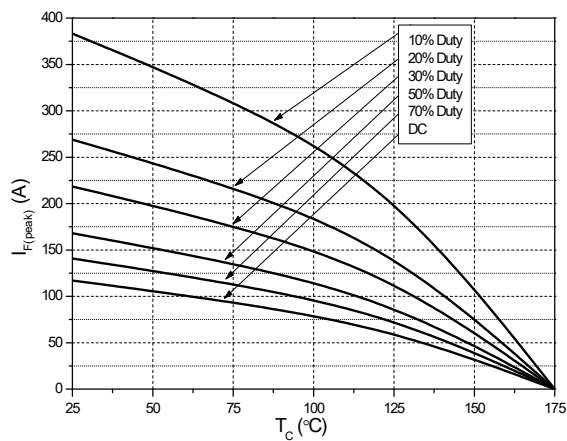


FIG.8: Current derating




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